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# 40-V, N-Channel NexFET™ Power MOSFETs

Check for Samples: CSD18502Q5B

### **FEATURES**

- · Ultra Low Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- Logic Level
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

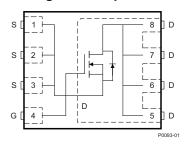
### **APPLICATIONS**

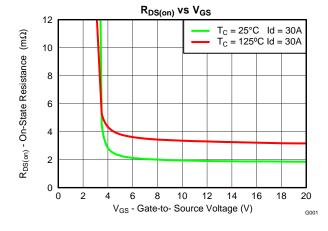
- DC-DC Conversion
- Secondary Side Synchronous Rectifier
- Motor Control

## **DESCRIPTION**

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.

Figure 1. Top View





### **PRODUCT SUMMARY**

$T_A = 25^\circ$	С	TYPICAL VA	UNIT		
$V_{DS}$	Drain to Source Voltage 40				
$Q_g$	Gate Charge Total (4.5V) 25				
$Q_{gd}$	Gate Charge Gate to Drain	8.4	nC		
D	Drain to Source On Resistance	$V_{GS} = 4.5V$	2.5	mΩ	
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = 10V 1.8		mΩ	
V <sub>GS(th)</sub>	Threshold Voltage 1.8				

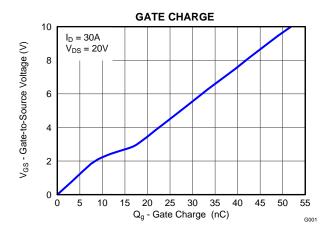
### **ORDERING INFORMATION**

Device	Package	Media	Qty	Ship
CSD18502Q5B	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

### **ABSOLUTE MAXIMUM RATINGS**

T <sub>A</sub> = 2	5°C	VALUE	UNIT
$V_{DS}$	Drain to Source Voltage	40	٧
$V_{GS}$	Gate to Source Voltage	±20	٧
	Continuous Drain Current (Package limited), $T_C = 25^{\circ}C$	100	
$I_D$	Continuous Drain Current (Silicon limited), $T_C = 25$ °C	204	Α
	Continuous Drain Current, T <sub>A</sub> = 25°C <sup>(1)</sup>	26	
$I_{DM}$	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	167	Α
P <sub>D</sub>	Power Dissipation <sup>(1)</sup>	3.2	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D = 88A, L = 0.1 mH, R_G = 25\Omega$	387	mJ

- (1) Typical  $R_{\theta JA} = 40^{\circ} \text{C/W}$  on a 1-inch $^2$  , 2-oz. Cu pad on a 0.06-inch thick FR4 PCB.
- (2) Pulse duration ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### **ELECTRICAL CHARACTERISTICS**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	naracteristics					
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	40			V
I <sub>DSS</sub>	Drain to Source Leakage Current	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 32V			1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = 20V$			100	nΑ
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.5	1.8	2.2	V
D	Drain to Course On Registeres	$V_{GS} = 4.5V, I_D = 30A$		2.5	3.3	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 30A$		1.8	2.3	mΩ
9 <sub>fs</sub>	Transconductance	$V_{DS} = 20V, I_D = 30A$		143		S
Dynamic	: Characteristics					
C <sub>iss</sub>	Input Capacitance			3900	5070	pF
C <sub>oss</sub>	Output Capacitance	$V_{GS} = 0V, V_{DS} = 20V, f = 1MHz$		900	1170	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			21	27	pF
$R_G$	Series Gate Resistance			1.2	2.4	Ω
Qg	Gate Charge Total (4.5V)			25	33	nC
$Q_g$	Gate Charge Total (10V)			52	68	nC
$Q_{gd}$	Gate Charge Gate to Drain	$V_{DS} = 20V, I_D = 30A$		8.4		nC
Q <sub>gs</sub>	Gate Charge Gate to Source			3900 900 21 1.2 25 52		nC
$Q_{g(th)}$	Gate Charge at Vth			6.9		nC
Q <sub>oss</sub>	Output Charge	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V		59		nC
t <sub>d(on)</sub>	Turn On Delay Time			5.3		ns
t <sub>r</sub>	Rise Time	$V_{DS} = 20V, V_{GS} = 10V,$		6.8		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$I_{DS} = 30A$ , $R_G = 0\Omega$		23		ns
t <sub>f</sub>	Fall Time	1		4		ns
Diode CI	haracteristics					
V <sub>SD</sub>	Diode Forward Voltage	$I_{SD} = 30A, V_{GS} = 0V$		0.8	1	V
$Q_{rr}$	Reverse Recovery Charge	V <sub>DS</sub> = 20V, I <sub>F</sub> = 30A,		88		nC
t <sub>rr</sub>	Reverse Recovery Time	di/dt = 300A/µs		44		ns

### THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case <sup>(1)</sup>			0.8	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (1)(2)			50	°C/W

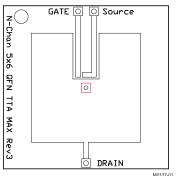
 $R_{\theta JC}$  is determined with the device mounted on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch x 1.5-inch (3.81-cm x 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB.  $R_{\theta JC}$  is specified by design, whereas  $R_{\theta JA}$  is determined by the user's board design. Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.

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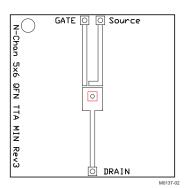
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Max  $R_{\theta JA} = 50^{\circ} C/W$  when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max  $R_{\theta JA} = 125^{\circ} C/W$  when mounted on a minimum pad area of 2-oz. (0.071-mm thick) Cu.

### TYPICAL MOSFET CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

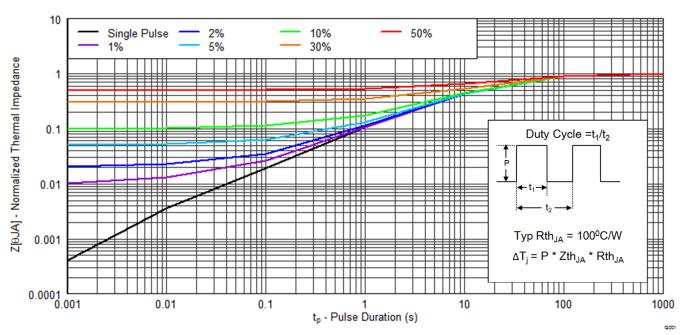


Figure 2. Transient Thermal Impedance

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### TEXAS INSTRUMENTS

## **TYPICAL MOSFET CHARACTERISTICS (continued)**

## (T<sub>A</sub> = 25°C unless otherwise stated)

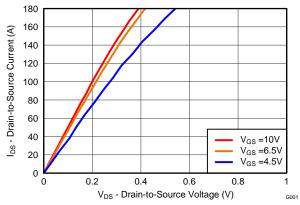


Figure 3. Saturation Characteristics

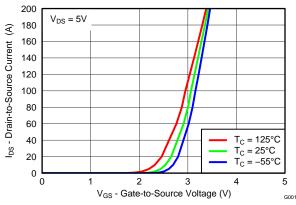


Figure 4. Transfer Characteristics

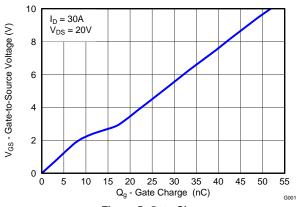


Figure 5. Gate Charge

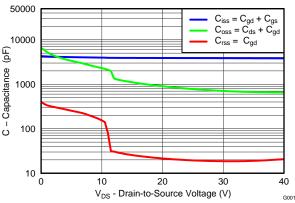


Figure 6. Capacitance

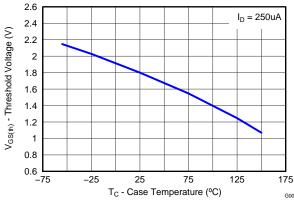


Figure 7. Threshold Voltage vs. Temperature

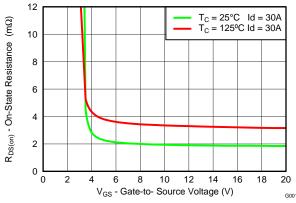


Figure 8. On-State Resistance vs. Gate-to-Source Voltage

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## TYPICAL MOSFET CHARACTERISTICS (continued)

(T<sub>A</sub> = 25°C unless otherwise stated)

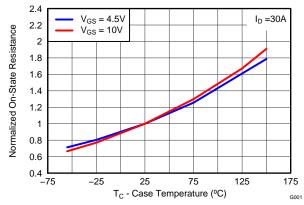


Figure 9. Normalized On-State Resistance vs. Temperature

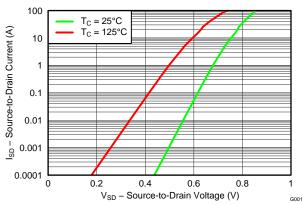


Figure 10. Typical Diode Forward Voltage

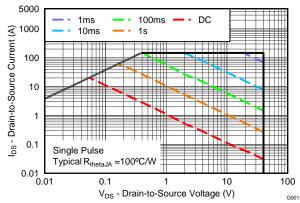


Figure 11. Maximum Safe Operating Area

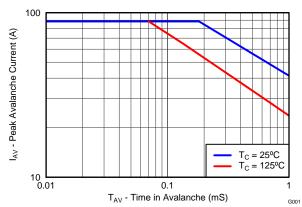


Figure 12. Single Pulse Unclamped Inductive Switching

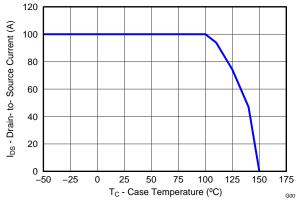


Figure 13. Maximum Drain Current vs. Temperature

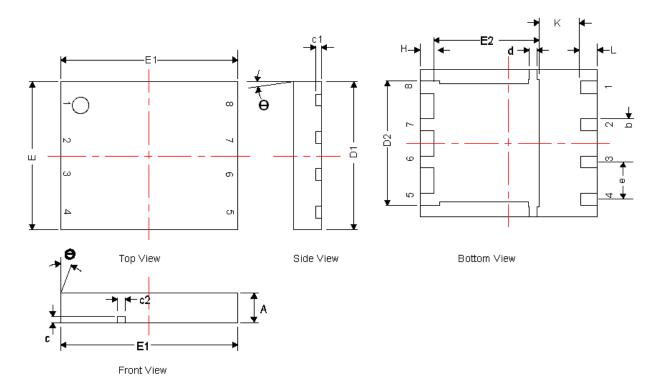
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## **MECHANICAL DATA**

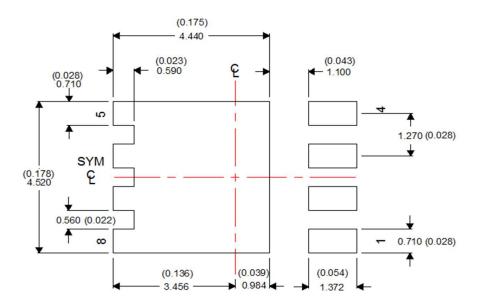
## **Q5B Package Dimensions**



DIM	MILLIMETERS							
DIM	MIN	NOM	MAX					
Α	0.95	1.00	1.05					
b	0.36	0.41	0.46					
С	0.15	0.20	0.25					
c1	0.15	0.20	0.25					
c2	0.20	0.25	0.30					
D1	4.90	5.00	5.10					
D2	4.12	4.22	4.32					
d	0.20	0.25	0.30					
E	4.90	5.00	5.10					
E1	5.90	6.00	6.10					
E2	3.48	3.58	3.68					
е		1.27 TYP						
L	0.46	0.56	0.66					
θ	0°	-	-					
K		1.40 TYP						

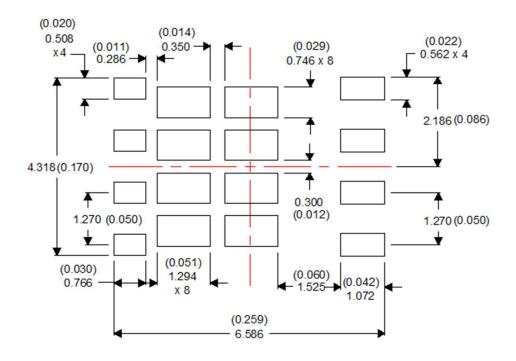
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### **Recommended PCB Pattern**



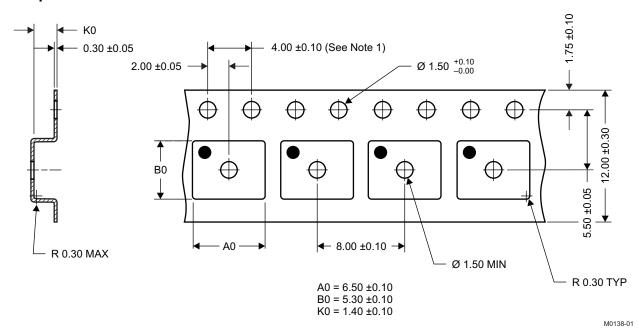
For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

## **Recommended Stencil Pattern**





## **Q5B Tape and Reel Information**



### Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket

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## PACKAGE OPTION ADDENDUM

21-Mar-2013

#### PACKAGING INFORMATION

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Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Top-Side Markings	Samples
CSD18502Q5B	ACTIVE	VSON	DNK	8	2500	Pb-Free (RoHS	CU SN	Level-1-260C-UNLIM		CSD18502	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Only one of markings shown within the brackets will appear on the physical device.

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## PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD18502Q5B	VSON	DNK	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

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### \*All dimensions are nominal

Device	Device Package Type		Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CSD18502Q5B	VSON	DNK	8	2500	335.0	335.0	32.0	

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